

PNP Type Bipolar Transistor

Features

- Low profile package
- Ideal for automated placement
- Power Dissipation of 200mW
- High Stability and High Reliability
- RoHS Compliant

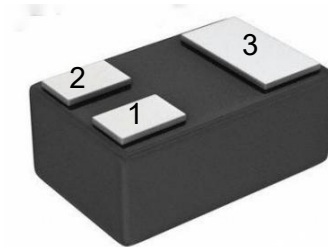
Mechanical Data

- Package: DFN1006-3L
- Lead Finish: Matte Tin
- Case Material: "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Tape Reel :10000pcs

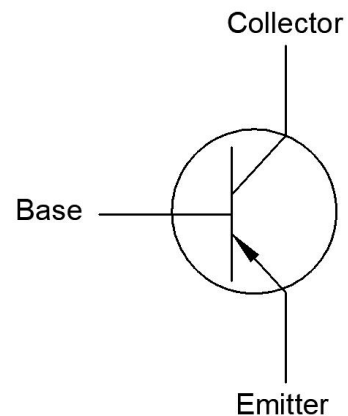
Applications

- amplifying signal
- Electronic switch
- Oscillating circuit
- variable resistance

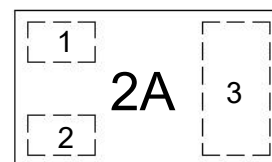
Appearance & Symbol



Package: DFN1006-3L
1: Base
2: Emitter
3: Collector



Marking Information



2A= Marking Code

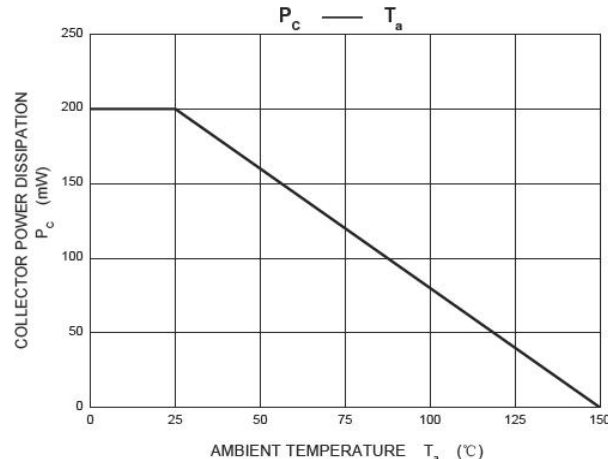
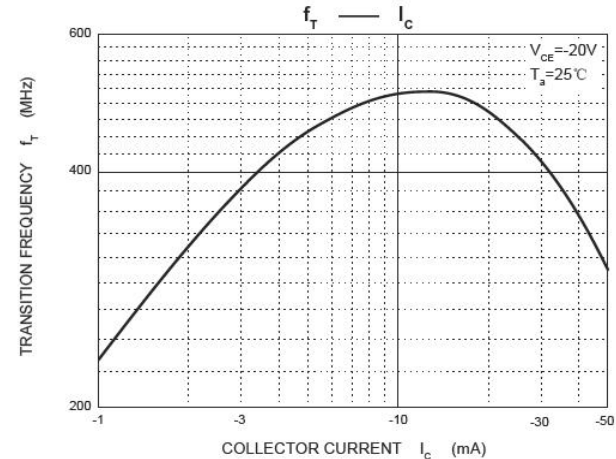
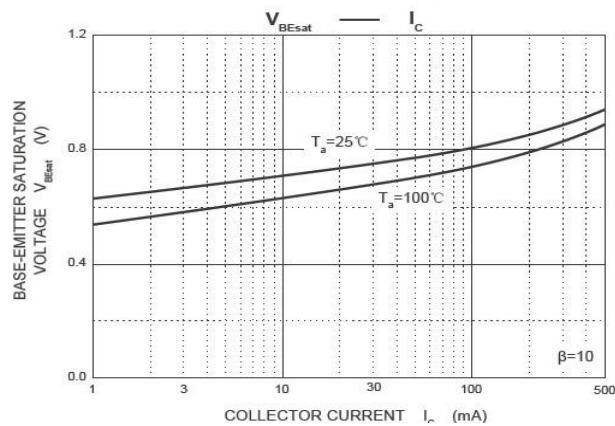
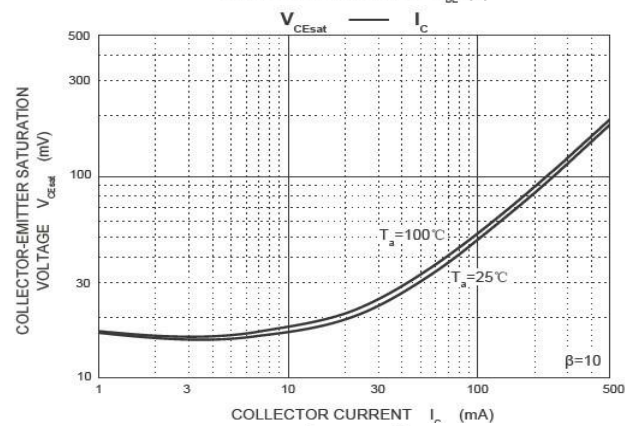
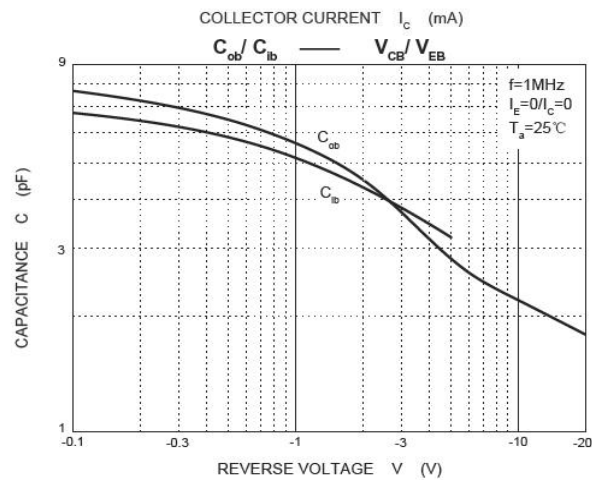
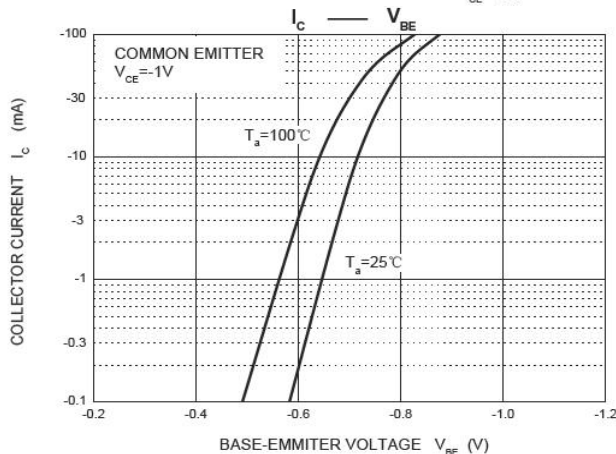
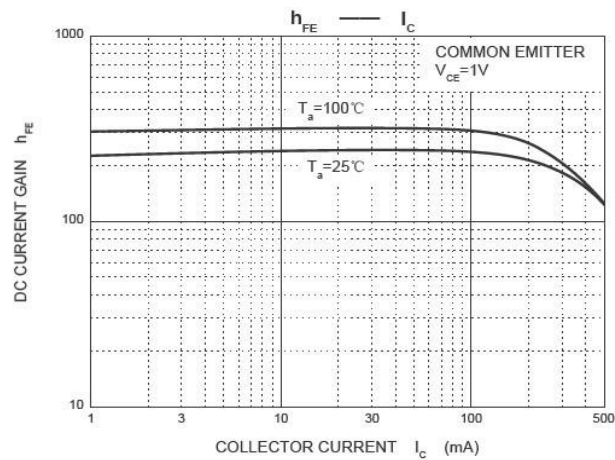
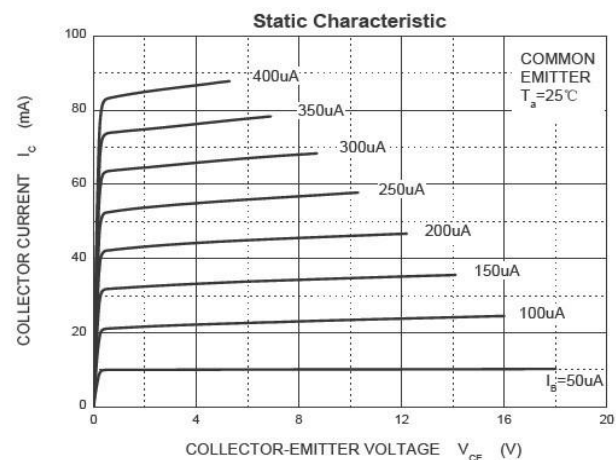
Absolute Maximum Ratings (T=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current - Continuous	I_C	-200	mA
Collector Power Dissipation	P_C	200	mW
Thermal Resistance From Junction to Ambient	$R_{\theta JA}$	625	°C/W
Junction Temperature	T_J	-55 to +150	°C
Junction and Storage Temperature	T_{STG}	-55 to +150	°C

Electrical Characteristics (T=25°C unless otherwise noted)

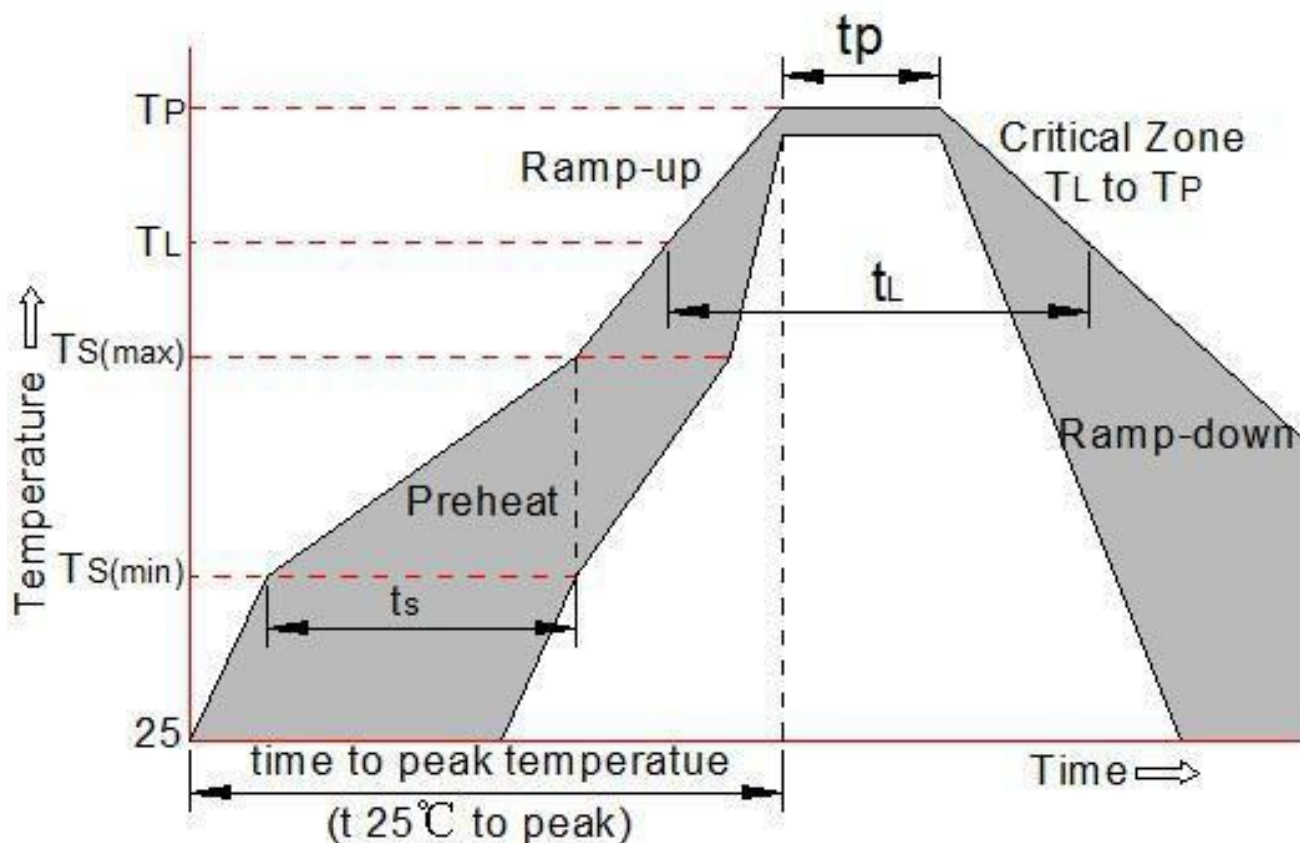
Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10\mu A, I_E = 0$	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-40		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu A, I_C = 0$	-5		V
Collector cut-off current	I_{CEX}	$V_{CE} = -30V, V_{BE(off)} = -3V$		-50	nA
Collector cut-off current	I_{CBO}	$V_{CB} = -40V, I_E = 0$		-100	nA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$		-100	nA
DC current gain	$h_{FE(1)}$	$V_{CE} = -1V, I_C = -10mA$	100	300	
	$h_{FE(2)}$	$V_{CE} = -1V, I_C = -50mA$	60		
	$h_{FE(3)}$	$V_{CE} = -2V, I_C = -100mA$	30		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -50mA, I_B = -5mA$		-0.3	V
Base -emitter saturation voltage	$V_{BE(sat)}$	$I_C = -50mA, I_B = -5mA$		-0.95	V
Transition frequency	f_T	$V_{CE} = -20V, I_C = -10mA, f = 100MHz$	300		MHz
Delay time	t_d	$V_{CC} = -3V, V_{BE} = -0.5V$ $I_C = -10mA, I_{B1} = I_{B2} = -1mA$		35	nS
Rise time	t_r			35	nS
Storage time	t_s	$V_{CC} = -3V, I_C = -10mA$ $I_{B1} = I_{B2} = -1mA$		225	nS
Fall time	t_f			75	nS

Typical Characteristics

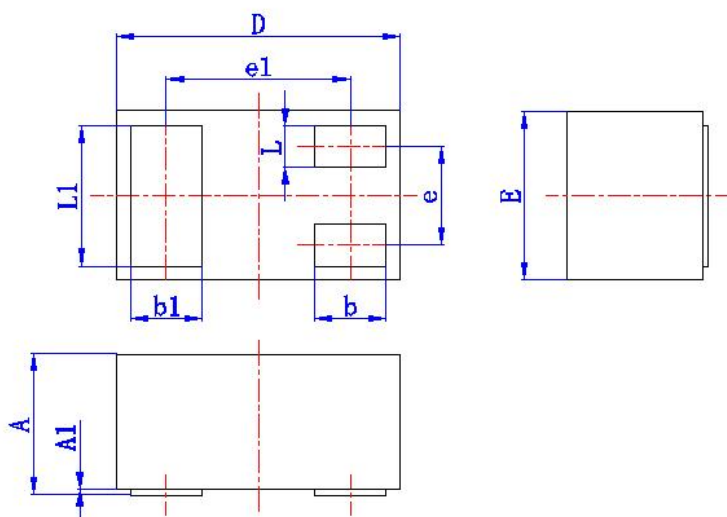


Soldering parameters

Reflow Condition		Pb-Free assembly (see as bellow)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150°C
	-Temperature Max($T_{s(max)}$)	+200°C
	-Time (Min to Max) (t_s)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3°C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature(T_L) (Liquid us)	+217°C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp (T_p)		8 min. Max
Do not exceed		+260°C

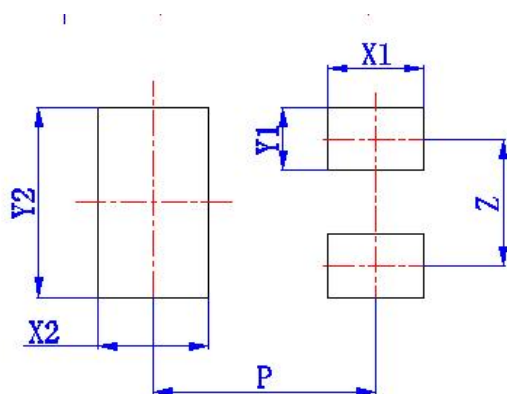


Package mechanical data

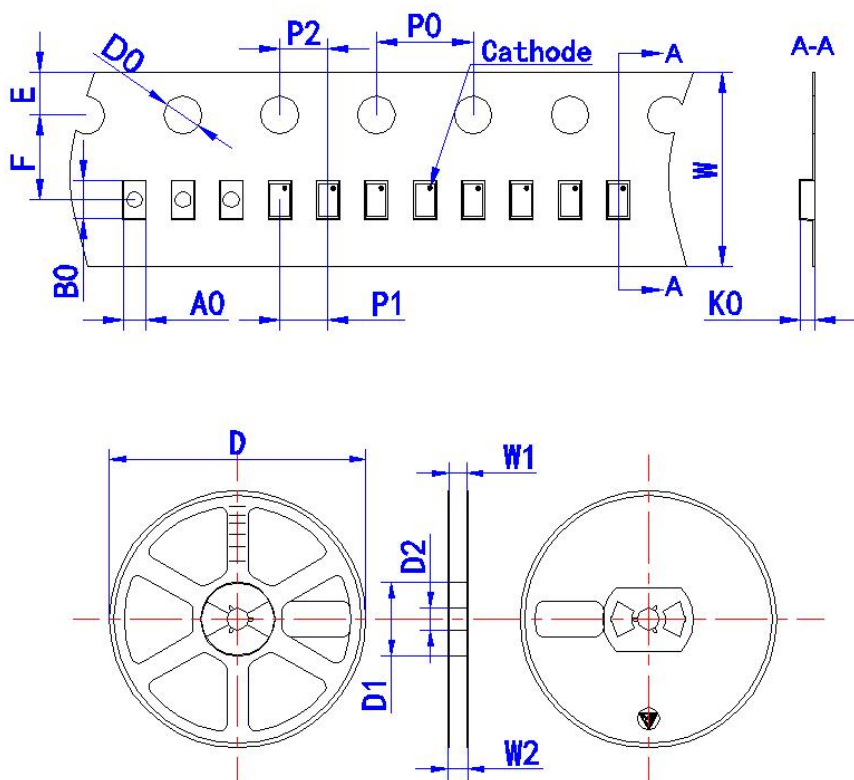


Symbol	Millimeters	
	min	max
A	0.4	0.52
A1	0	0.05
D	0.9	1.1
E	0.55	0.65
e	(0.35)	
e1	(0.65)	
b	0.2	0.3
b1	0.2	0.3
L	0.1	0.2
L1	0.45	0.55

Suggested Land Pattern



Symbol	Dimension in Millimeters
	typ
X1	(0.3)
X2	(0.35)
Y1	(0.2)
Y2	(0.6)
Z	(0.4)
P	(0.7)



Symbol	Dimension in Millimeters
Tape	
A0	0.71±0.05
B0	1.16±0.05
K0	0.60±0.05
D0	1.55±0.05
E	1.75±0.10
F	3.50±0.10
P0	4.00±0.10
P1	2.00±0.10
P2	2.00±0.05
W	8.00+0.3/-0.1
Reel	
D	178.0±2.00
D1	54.40±1.00
D2	13.00±1.00
W1	9.50±1.00
W2	12.30±1.00